

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L3	272173	(nitride or oxynitride or (hard near3 mask\$4) SiN or SiON)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/28 10:46
2	BRS	L4	361338	photoresist or resist or BARC	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/28 10:46
3	BRS	L5	8775	((nitride or oxynitride or (hard near3 mask\$4) SiN or SiON)) near8 (photoresist or resist or BARC)) near8 (remov\$4 or etch\$4 or strip\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/28 10:47
4	BRS	L6	1765	((((nitride or oxynitride or (hard near3 mask\$4) SiN or SiON)) near8 (photoresist or resist or BARC)) near8 (remov\$4 or etch\$4 or strip\$4)) same plasma	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/28 10:47
5	BRS	L9	873	((nitride or oxynitride or (hard near3 mask\$4) SiN or SiON)) near8 (photoresist or resist or BARC)) near8 (remov\$4 or etch\$4 or strip\$4) near8 plasma	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/28 10:49

	Typ	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L11	3604	(coat or coated or coating or fill or filling or filled) near4 (sacrificial or photoresist or resist) near8 (gap or gaps or hole or holes or trench or trenches or aperture or apertures or via or vias)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/28 11:03
7	BRS	L12	2132	(plasma near3 (etch or etching or etched or strip or stripping or stripped)) near8 ("hard mask" or "silicon nitride" or "silicon oxynitride" or SiN or SiON)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/28 11:04
8	BRS	L13	51	11 and 12	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/28 11:23
9	IS&R	L14	437	(438/738).CCLS.	USPAT; US-PGP UB	2003/06/28 11:24
10	IS&R	L19	177	(438/717).CCLS.	USPAT; US-PGP UB	2003/06/28 15:10